

## BUK9832-55A-VB Datasheet

# N-Channel 60-V (D-S) MOSFET

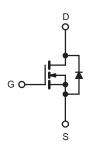
PRODU	ICT SUMMARY	
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)
60	0.028 at V <sub>GS</sub> = 10 V	7.0
60	0.033 at V <sub>GS</sub> = 4.5 V	5.6

#### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFETs
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC







N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	Γ <sub>A</sub> = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		$V_{DS}$	6	0	V
Gate-Source Voltage		$V_{GS}$	± 20		V
Continuous Drain Current (T <sub>.I</sub> = 175 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	I <sub>D</sub>	7.0	6.0	
Continuous Dialii Curient (1) = 175 C)	T <sub>A</sub> = 70 °C		6.1	5.0	Α
Pulsed Drain Current		I <sub>DM</sub>	4	0	^
Avalanche Current		I <sub>AS</sub>	1	5	
Single Pulse Avalanche Energy	E <sub>AS</sub>	11		mJ	
Maximum Dayyar Dissination	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.3	1.7	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	' D	2.3	1.2	VV
Operating Junction and Storage Temperature Range	је	T <sub>J</sub> , T <sub>stg</sub>	- 55 t	o 175	°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Mariana la sation to Ambient 3	t ≤ 10 s	- R <sub>thJA</sub>	36	45		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		75	90	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	17	20		

### Notes:

a. Surface Mounted on 1" x 1" FR4 board.

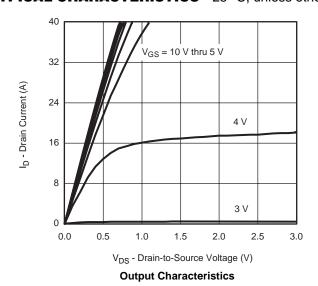


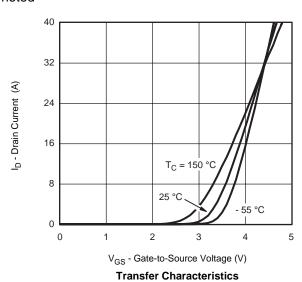
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				•			
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1		3	V	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zara Cata Valtaga Drain Current		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$	V 1		1	^	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			20	μA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α	
		$V_{GS} = 10 \text{ V}, I_D = 6.0 \text{ A}$		0.028			
	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_D = 6.0 \text{ A}, T_J = 125 \text{ °C}$		0.032		Ω	
Drain-Source On-State Resistance <sup>a</sup>		$V_{GS} = 10 \text{ V}, I_D = 6.0 \text{ A}, T_J = 175 ^{\circ}\text{C}$		0.040			
		$V_{GS} = 4.5 \text{ V}, I_D = 5.1 \text{ A}$		0.033			
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_D = 6.0 \text{ A}$		25		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 1.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V	
Dynamic <sup>b</sup>	<u>'</u>		l		<u> </u>		
Total Gate Charge	$Q_g$			18	27		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 6.0 \text{ A}$		3.4		nC	
Gate-Drain Charge	$Q_{gd}$			5.3			
Gate Resistance	$R_{g}$	$V_{GS} = 0.1 \text{ V}, f = 5 \text{ MHz}$	0.5	1.4	2.4	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			10	20		
Rise Time	t <sub>r</sub>	$V_{DD} = 30 \text{ V}, R_L = 30 \Omega$		10	20		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ 1 A, $V_{GEN}$ = 10 V, $R_g$ = 6 $\Omega$		25	50	ns	
Fall Time	t <sub>f</sub>			12	24		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 1.7 A, dl/dt = 100 A/μs		50	80		

#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

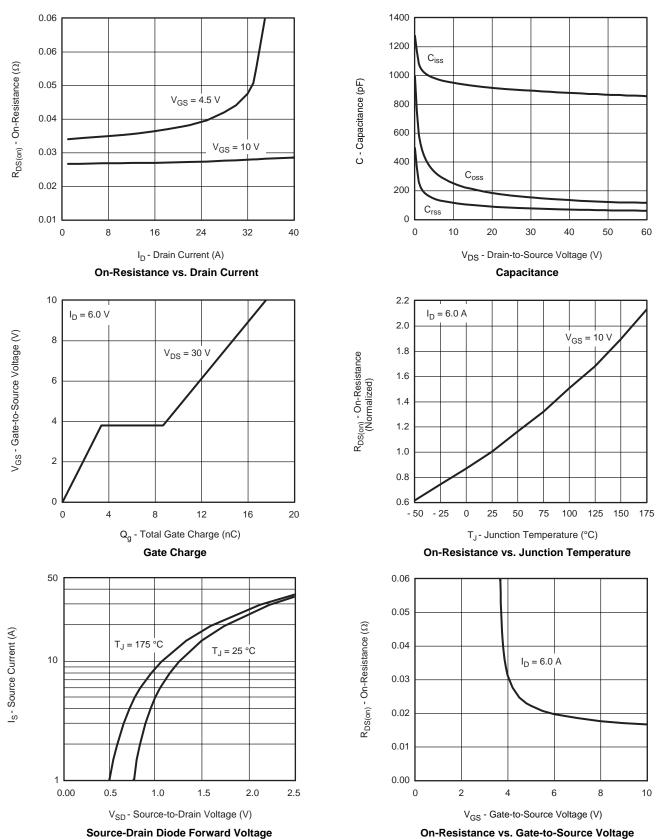
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







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0.1

0.05 0.02

Single Pulse

10-3

0.1

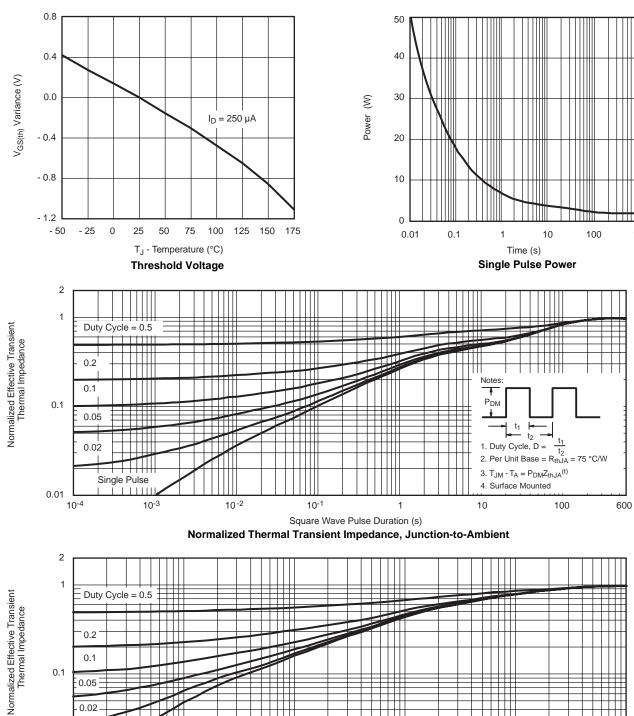
0.01 10-4



1000

10

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

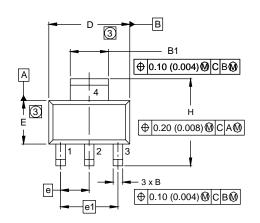


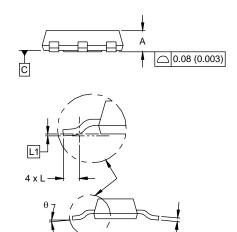
Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Foot

10-1



## **SOT-223 (HIGH VOLTAGE)**





DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
Α	1.55	1.80	0.061	0.071
В	0.65	0.85	0.026	0.033
B1	2.95	3.15	0.116	0.124
С	0.25	0.35	0.010	0.014
D	6.30	6.70	0.248	0.264
E	3.30	3.70	0.130	0.146
е	2.30 BSC		0.0905	BSC
e1	4.60 BSC		0.181	BSC
Н	6.71	7.29	0.264	0.287
L	0.91	-	0.036	-
L1	0.061 BSC		0.0024	BSC
θ	-	10'	-	10'

ECN: S-82109-Rev. A, 15-Sep-08

DWG: 5969

#### Notes

- 1. Dimensioning and tolerancing per ASME Y14.5M-1994.
- 2. Dimensions are shown in millimeters (inches).
- 3. Dimension do not include mold flash.
- 4. Outline conforms to JEDEC outline TO-261AA.



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